Wladyslaw

List of Publications by Year in descending order

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470 papers	23,020 citations	10979 71 h-index	10724 138 g-index
475 all docs	475 docs citations	475 times ranked	11038 citing authors

#	Article	IF	Citations
1	Band Anticrossing in GaInNAs Alloys. Physical Review Letters, 1999, 82, 1221-1224.	2.9	1,540
2	Unusual properties of the fundamental band gap of InN. Applied Physics Letters, 2002, 80, 3967-3969.	1.5	1,380
3	Superior radiation resistance of In1â^'xGaxN alloys: Full-solar-spectrum photovoltaic material system. Journal of Applied Physics, 2003, 94, 6477-6482.	1.1	572
4	Small band gap bowing in In1â^'xGaxN alloys. Applied Physics Letters, 2002, 80, 4741-4743.	1.5	563
5	Effect of the location of Mn sites in ferromagneticGa1â^'xMnxAson its Curie temperature. Physical Review B, 2002, 65, .	1.1	491
6	Electron mobility in modulation-doped heterostructures. Physical Review B, 1984, 30, 4571-4582.	1.1	428
7	Temperature dependence of the fundamental band gap of InN. Journal of Applied Physics, 2003, 94, 4457-4460.	1.1	375
8	Effects of the narrow band gap on the properties of InN. Physical Review B, 2002, 66, .	1.1	374
9	Valence-band anticrossing in mismatched III-V semiconductor alloys. Physical Review B, 2007, 75, .	1.1	354
10	Intrinsic limitations to the doping of wide-gap semiconductors. Physica B: Condensed Matter, 2001, 302-303, 123-134.	1.3	314
11	Band anticrossing in highly mismatched IIIÂV semiconductor alloys. Semiconductor Science and Technology, 2002, 17, 860-869.	1.0	298
12	Valence band anticrossing in GaBixAs1â^'x. Applied Physics Letters, 2007, 91, .	1.5	296
13	Electron mobility and free-carrier absorption in InP; determination of the compensation ratio. Journal of Applied Physics, 1980, 51, 2659.	1.1	289
14	Engineering the Electronic Band Structure for Multiband Solar Cells. Physical Review Letters, 2011, 106, 028701.	2.9	282
15	Amphoteric native defects in semiconductors. Applied Physics Letters, 1989, 54, 2094-2096.	1.5	281
16	Origin of the 0.82â€eV electron trap in GaAs and its annihilation by shallow donors. Applied Physics Letters, 1982, 40, 342-344.	1.5	278
17	Nature of room-temperature photoluminescence in ZnO. Applied Physics Letters, 2005, 86, 191911.	1.5	274
18	Diluted II-VI Oxide Semiconductors with Multiple Band Gaps. Physical Review Letters, 2003, 91, 246403.	2.9	268

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19	Electron mobility and freeâ€carrier absorption in GaAs: Determination of the compensation ratio. Journal of Applied Physics, 1979, 50, 899-908.	1.1	246
20	Native point defects in lowâ€temperatureâ€grown GaAs. Applied Physics Letters, 1995, 67, 279-281.	1.5	242
21	Large, nitrogen-induced increase of the electron effective mass in InyGa1â^'yNxAs1â^'x. Applied Physics Letters, 2000, 76, 2409-2411.	1.5	236
22	Structure and electronic properties of InN and In-rich group III-nitride alloys. Journal Physics D: Applied Physics, 2006, 39, R83-R99.	1.3	229
23	Nature of the fundamental band gap in GaNxP1â^'x alloys. Applied Physics Letters, 2000, 76, 3251-3253.	1.5	228
24	Effects of electron concentration on the optical absorption edge of InN. Applied Physics Letters, 2004, 84, 2805-2807.	1.5	221
25	Electron mobility inAlxGa1â^'xN/GaNheterostructures. Physical Review B, 1997, 56, 1520-1528.	1.1	204
26	Interaction of Localized Electronic States with the Conduction Band: Band Anticrossing in II-VI Semiconductor Ternaries. Physical Review Letters, 2000, 85, 1552-1555.	2.9	195
27	Raman Spectroscopy and Time-Resolved Photoluminescence of BN and BxCyNzNanotubes. Nano Letters, 2004, 4, 647-650.	4.5	194
28	Evidence forp-Type Doping of InN. Physical Review Letters, 2006, 96, 125505.	2.9	193
29	Finite element simulations of compositionally graded InGaN solar cells. Solar Energy Materials and Solar Cells, 2010, 94, 478-483.	3.0	192
30	Fermi-level stabilization energy in group III nitrides. Physical Review B, 2005, 71, .	1.1	190
31	Fano interference of the Raman phonon in heavily boronâ€doped diamond films grown by chemical vapor deposition. Applied Physics Letters, 1995, 66, 616-618.	1.5	177
32	Controlling the Curie temperature in (Ga,Mn)As through location of the Fermi level within the impurity band. Nature Materials, 2012, 11, 444-449.	13.3	168
33	Band gaps of InN and group III nitride alloys. Superlattices and Microstructures, 2003, 34, 63-75.	1.4	159
34	Persistent photoconductivity in n-type GaN. Applied Physics Letters, 1997, 71, 1098-1100.	1.5	158
35	Optical properties and electronic structure of InN and In-rich group III-nitride alloys. Journal of Crystal Growth, 2004, 269, 119-127.	0.7	157
36	Band-edge hydrostatic deformation potentials in III-V semiconductors. Physical Review Letters, 1987, 59, 501-504.	2.9	156

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37	Metastability of Oxygen Donors in AlGaN. Physical Review Letters, 1998, 80, 4008-4011.	2.9	154
38	Effect of nitrogen on the band structure of GaInNAs alloys. Journal of Applied Physics, 1999, 86, 2349-2351.	1.1	153
39	Mechanism of Fermi-level stabilization in semiconductors. Physical Review B, 1988, 37, 4760-4763.	1.1	151
40	Modeling of InGaN/Si tandem solar cells. Journal of Applied Physics, 2008, 104, .	1.1	139
41	Optical properties of InxGa1â^'xN alloys grown by metalorganic chemical vapor deposition. Journal of Applied Physics, 1998, 84, 4452-4458.	1.1	135
42	Effect of polarization fields on transport properties in AlGaN/GaN heterostructures. Journal of Applied Physics, 2001, 89, 1783.	1.1	132
43	Multiband GaNAsP quaternary alloys. Applied Physics Letters, 2006, 88, 092110.	1.5	128
44	Reconfiguring crystal and electronic structures of MoS2 by substitutional doping. Nature Communications, 2018, 9, 199.	5.8	128
45	Band Anticrossing in III-N-V Alloys. Physica Status Solidi (B): Basic Research, 2001, 223, 75-85.	0.7	119
46	Role of nitrogen in the reduced temperature dependence of band-gap energy in GaNAs. Applied Physics Letters, 2000, 77, 3021-3023.	1.5	118
47	Dependence of the fundamental band gap of AlxGa1â^'xN on alloy composition and pressure. Journal of Applied Physics, 1999, 85, 8505-8507.	1.1	112
48	Annealing studies of lowâ€temperatureâ€grown GaAs:Be. Journal of Applied Physics, 1992, 71, 1699-1707.	1.1	111
49	Two-photon excitation in an intermediate band solar cell structure. Applied Physics Letters, 2012, 100, .	1.5	110
50	Universal bandgap bowing in group-III nitride alloys. Solid State Communications, 2003, 127, 411-414.	0.9	104
51	Mechanism of Schottky barrier formation: The role of amphoteric native defects. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1987, 5, 1062.	1.6	103
52	On the crystalline structure, stoichiometry and band gap of InN thin films. Applied Physics Letters, 2005, 86, 071910.	1.5	103
53	Reduction of band-gap energy in GaNAs and AlGaNAs synthesized by N+ implantation. Applied Physics Letters, 1999, 75, 1410-1412.	1.5	102
54	Effect of nitrogen on the electronic band structure of group III-N-V alloys. Physical Review B, 2000, 62, 4211-4214.	1.1	101

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55	Large disparity between gallium and antimony self-diffusion in gallium antimonide. Nature, 2000, 408, 69-72.	13.7	100
56	Simultaneous Enhancement of Electrical Conductivity and Thermopower of Bi₂Te₃ by Multifunctionality of Native Defects. Advanced Materials, 2015, 27, 3681-3686.	11.1	97
57	Fermi level dependent native defect formation: Consequences for metalâ€“semiconductor and semiconductorâ€“semiconductor interfaces. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1988, 6, 1257.	1.6	92
58	Growth of a-plane InN on r-plane sapphire with a GaN buffer by molecular-beam epitaxy. Applied Physics Letters, 2003, 83, 1136-1138.	1.5	91
59	Curie temperature limit in ferromagneticGa1â^'xMnxAs. Physical Review B, 2003, 68, .	1.1	91
60	Minorityâ€carrier mobility inpâ€type GaAs. Journal of Applied Physics, 1979, 50, 5040-5042.	1.1	88
61	Electron mobility in nâ€type GaAs at 77 K: Determination of the compensation ratio. Journal of Applied Physics, 1982, 53, 769-770.	1.1	88
62	Existence and removal of Cu2Se second phase in coevaporated Cu2ZnSnSe4 thin films. Journal of Applied Physics, 2012, 111, .	1.1	87
63	Valence band hybridization inN-richGaN1â^'xAsxalloys. Physical Review B, 2004, 70, .	1.1	86
64	Ideal transparent conductors for full spectrum photovoltaics. Journal of Applied Physics, 2012, 111, .	1.1	86
65	Effect of band anticrossing on the optical transitions inGaAs1â^'xNx/GaAsmultiple quantum wells. Physical Review B, 2001, 64, .	1.1	83
66	Pressure-dependent photoluminescence study of ZnO nanowires. Applied Physics Letters, 2005, 86, 153117.	1.5	83
67	Synthesis and optical properties of II-O-VI highly mismatched alloys. Journal of Applied Physics, 2004, 95, 6232-6238.	1.1	82
68	Local-vibrational-mode spectroscopy ofDXcenters in Si-doped GaAs under hydrostatic pressure. Physical Review Letters, 1991, 66, 774-777.	2.9	81
69	Carrier localization of as-grownn-type gallium nitride under large hydrostatic pressure. Physical Review B, 1996, 53, 1322-1326.	1.1	76
70	Effect of oxygen on the electronic band structure in ZnOxSe1â^'x alloys. Applied Physics Letters, 2003, 83, 299-301.	1.5	76
71	Band structure of highly mismatched semiconductor alloys:â€ƒCoherent potential approximation. Physical Review B, 2002, 65, .	1.1	74
72	GermaniumGe70/74Ge isotope heterostructures: An approach to self-diffusion studies. Physical Review B, 1995, 51, 16817-16821.	1.1	71

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73	In1â^'xMnxSbâ€"a narrow-gap ferromagnetic semiconductor. Applied Physics Letters, 2003, 82, 4310-4312.	1.5	71
74	Electronic Band Structure of<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:msub><mml:mrow><mml:mi>GaN</mml:mi></mml:mrow><mml:mrow><mml:mi>x</mml:mi></mml:mrow></mml:msub><mml:msub><mml:mrow><mml:mi mathvariant="normal">P</mml:mi></mml:mrow><mml:mrow><mml:mi>y</mml:mi></mml:mrow></mml:msub><mml:msub><mml:mro Physical Review Applied, 2014, 1, .	1.5	71
75	Enhancement of Curie temperature in Ga1â^'xMnxAs/Ga1â^'yAlyAs ferromagnetic heterostructures by Be modulation doping. Applied Physics Letters, 2003, 83, 4220-4222.	1.5	70
76	Pressure dependence of the fundamental band-gap energy of CdSe. Applied Physics Letters, 2004, 84, 67-69.	1.5	70
77	Interband optical absorption in free standing layer of Ga0.96In0.04As0.99N0.01. Applied Physics Letters, 2000, 76, 1279-1281.	1.5	68
78	Band anticrossing inGaP1â^'xNxalloys. Physical Review B, 2002, 65, .	1.1	67
79	Origin of the large band-gap bowing in highly mismatched semiconductor alloys. Physical Review B, 2003, 67, .	1.1	67
80	Effects of Quantum Confinement on the Doping Limit of Semiconductor Nanowires. Nano Letters, 2007, 7, 1186-1190.	4.5	67
81	Band gap bowing parameter of In1â^'xAlxN. Journal of Applied Physics, 2008, 104, .	1.1	67
82	Hole transport and photoluminescence in Mg-doped InN. Journal of Applied Physics, 2010, 107, .	1.1	67
83	Band anticrossing in highly mismatched<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:msub><mml:mi mathvariant="normal">Sn</mml:mi><mml:mi>x</mml:mi></mml:msub><mml:msub><mml:mi mathvariant="normal">Ge</mml:mi><mml:mrow><mml:mn>1</mml:mn><mml:mo>â^'</mml:mo><mml:mi>x</mml:mi></mml:mrow alloys. Physical Review B, 2008, 77, .	1.1	66
84	Fermi level stabilization energy in cadmium oxide. Journal of Applied Physics, 2010, 107, .	1.1	66
85	Carrier scattering by native defects in heavily doped semiconductors. Physical Review B, 1990, 41, 10218-10220.	1.1	65
86	Nitrogen-induced increase of the maximum electron concentration in group III-N-V alloys. Physical Review B, 2000, 61, R13337-R13340.	1.1	65
87	Hydrostatic pressure dependence of the fundamental bandgap of InN and In-rich group III nitride alloys. Applied Physics Letters, 2003, 83, 4963-4965.	1.5	65
88	Demonstration of a IIIâ€"Nitride/Silicon Tandem Solar Cell. Applied Physics Express, 2009, 2, 122202.	1.1	64
89	Phosphorus antisite defects in low-temperature InP. Physical Review B, 1993, 47, 4111-4114.	1.1	63
90	Band structure and optical properties ofInyGa1â^'yAs1â^'xNxalloys. Physical Review B, 2001, 65, .	1.1	63

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91	Current status of research and development of IIIÂNÂV semiconductor alloys. Semiconductor Science and Technology, 2002, 17, 741-745.	1.0	61
92	Effects of surface states on electrical characteristics of InN andIn1â^'xGaxN. Physical Review B, 2007, 76, .	1.1	61
93	Highly mismatched crystalline and amorphous GaN1â^'xAsx alloys in the whole composition range. Journal of Applied Physics, 2009, 106, .	1.1	61
94	Photocurrent induced by two-photon excitation in ZnTeO intermediate band solar cells. Applied Physics Letters, 2013, 102, .	1.5	61
95	Molecular beam epitaxial growth and optical properties of highly mismatched ZnTe1â^'xOx alloys. Applied Physics Letters, 2012, 100, .	1.5	60
96	Crystal structure and properties of CdxZn1â^'xO alloys across the full composition range. Applied Physics Letters, 2013, 102, .	1.5	60
97	High quality InN/GaN heterostructures grown by migration enhanced metalorganic chemical vapor deposition. Applied Physics Letters, 2004, 84, 1892-1894.	1.5	59
98	Structural analysis of ferromagnetic Mn-doped ZnO thin films deposited by radio frequency magnetron sputtering. Journal of Applied Physics, 2005, 97, 126107.	1.1	59
99	Effects of piezoelectric field on defect formation, charge transfer, and electron transport at GaN/AlxGa1â^'xN interfaces. Applied Physics Letters, 1998, 73, 339-341.	1.5	57
100	Band structure engineering of ZnO1â^'xSex alloys. Applied Physics Letters, 2010, 97, .	1.5	56
101	Defect formation and diffusion in heavily doped semiconductors. Physical Review B, 1994, 50, 5221-5225.	1.1	55
102	Mutual passivation of electrically active and isovalent impurities. Nature Materials, 2002, 1, 185-189.	13.3	55
103	Mgâ€doped InN and InGaN â€“ Photoluminescence, capacitanceâ€“voltage and thermopower measurements. Physica Status Solidi (B): Basic Research, 2008, 245, 873-877.	0.7	55
104	Effects of Free Carriers on the Optical Properties of Doped CdO for Full-Spectrum Photovoltaics. Physical Review Applied, 2016, 6, .	1.5	54
105	Electron mobility in InN and III-N alloys. Journal of Applied Physics, 2007, 102, 073705.	1.1	52
106	Acoustic phonon scattering of two-dimensional electrons in GaN/AlGaN heterostructures. Applied Physics Letters, 2002, 80, 1228-1230.	1.5	51
107	Formation of Mn-derived impurity band in III-Mn-V alloys by valence band anticrossing. Physical Review B, 2008, 78, .	1.1	50
108	Structure-Dependent Hydrostatic Deformation Potentials of Individual Single-Walled Carbon Nanotubes. Physical Review Letters, 2004, 93, .	2.9	49

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109	Arsenic antisite-related defects in low-temperature MBE grown GaAs. Semiconductor Science and Technology, 1992, 7, 1037-1041.	1.0	48
110	Determination of free hole concentration in ferromagnetic Ga1â^'xMnxAs using electrochemical capacitanceâ€“voltage profiling. Applied Physics Letters, 2002, 81, 844-846.	1.5	48
111	Synthesis of GaNxAs1â^'x thin films by pulsed laser melting and rapid thermal annealing of N+-implanted GaAs. Journal of Applied Physics, 2003, 94, 1043-1049.	1.1	48
112	Structural and electronic properties of amorphous and polycrystalline In2Se3 films. Journal of Applied Physics, 2003, 94, 2390-2397.	1.1	48
113	Synthesis of InNxP1â^'x thin films by N ion implantation. Applied Physics Letters, 2001, 78, 1077-1079.	1.5	46
114	Electronic structure of<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:msub><mml:mrow><mml:mtext>Ga</mml:mtext></mml:mrow><mml:mrow><mml:mn	1.1	46
115	Mechanisms of Schottky Barrier Control on n-Type Germanium Using Ge3N4 Interlayers. Journal of the Electrochemical Society, 2011, 158, H358.	1.3	46
116	Fermi-level stabilization in the topological insulators<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:msub><mml:mtext>Bi</mml:mtext><mml:mn>2</mml:mn></mml:msub><mml:msub><mml:mtext>Se</mml:mtext><mml:mn>3</mml:mn></mml:msub><mml:msub><mml:mtext>Bi</mml:mtext><mml:mn>2</mml:mn></mml:msub><mml:msub><mml:mtext>Te</mml:mtext><mml:mn>3</mml:mn></mml:msub></mml:math>. Physical Review B, 2014, 89, .	1.1	45
117	Mg doped InN and confirmation of free holes in InN. Applied Physics Letters, 2011, 98, 042104.	1.5	44
118	Growth and characterization of ZnO1â^'xSx highly mismatched alloys over the entire composition. Journal of Applied Physics, 2015, 118, .	1.1	43
119	Theoretical transport studies of p-type GaN/AlGaN modulation-doped heterostructures. Applied Physics Letters, 1999, 74, 2405-2407.	1.5	42
120	Formation of diluted IIIâ€“V nitride thin films by N ion implantation. Journal of Applied Physics, 2001, 90, 2227-2234.	1.1	42
121	Compensating point defects inHe+4-irradiated InN. Physical Review B, 2007, 75, .	1.1	42
122	Effects of point defects on thermal and thermoelectric properties of InN. Applied Physics Letters, 2011, 98, .	1.5	42
123	Demonstration of homojunction ZnTe solar cells. Journal of Applied Physics, 2010, 108, .	1.1	40
124	Origin ofnâ€type conductivity of lowâ€temperature grown InP. Journal of Applied Physics, 1994, 76, 600-602.	1.1	38
125	Transport-to-quantum lifetime ratios in AlGaN/GaN heterostructures. Applied Physics Letters, 2002, 80, 2508-2510.	1.5	38
126	Band-gap bowing effects in BxGa1â^'xAs alloys. Journal of Applied Physics, 2003, 93, 2696-2699.	1.1	38

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127	Shallow donor associated with the main electron trap (EL2) in meltâ€grown GaAs. Applied Physics Letters, 1983, 43, 112-114.	1.5	37
128	Pressure dependence of Schottky barrier height at the Pt/GaAs interface. Applied Physics Letters, 1988, 53, 974-976.	1.5	37
129	Annealing of AsGa-related defects in LT-GaAs: The role of gallium vacancies. Journal of Electronic Materials, 1993, 22, 1401-1404.	1.0	37
130	Electron cyclotron effective mass in indium nitride. Applied Physics Letters, 2010, 96, .	1.5	37
131	Demonstration of ZnTe_{1-x}O_x Intermediate Band Solar Cell. Japanese Journal of Applied Physics, 2011, 50, 082304.	0.8	37
132	GaNAsP: An intermediate band semiconductor grown by gas-source molecular beam epitaxy. Applied Physics Letters, 2013, 102, .	1.5	37
133	Fermi level stabilization and band edge energies in CdxZn1â^'xO alloys. Journal of Applied Physics, 2014, 115, .	1.1	37
134	Lattice location of diffused Zn atoms in GaAs and InP single crystals. Journal of Applied Physics, 1991, 69, 2998-3006.	1.1	36
135	Growth and properties of ferromagnetic In1â^'Mn Sb alloys. Physica E: Low-Dimensional Systems and Nanostructures, 2004, 20, 325-332.	1.3	36
136	Characterization of low-temperature molecular-beam-epitaxy grown GaBiAs layers. Semiconductor Science and Technology, 2007, 22, 819-823.	1.0	36
137	Full multiple-scattering analysis of XANES at the <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:mtext>Cd</mml:mtext><mml:mtext>â€‰</mml:mtext><mml:msub><mml:mi>L</mml:mi><mml:mn> xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:mtext>O</mml:mtext><mml:mtext>â€‰</mml:mtext><mml:mi>K</mml:mi></mml:mrow></mml: in CdO films combined with a soft-x-ray emission investigation. Physical Review B, 2010, 82, .	1.1	36
138	Formation of aDXcenter in InP under hydrostatic pressure. Physical Review Letters, 1992, 68, 3619-3622.	2.9	35
139	Coimplantation and electrical activity of C in GaAs: Stoichiometry and damage effects. Applied Physics Letters, 1992, 60, 2383-2385.	1.5	35
140	Dislocation density reduction by isoelectronic impurities in semiconductors. Applied Physics Letters, 1989, 54, 2009-2011.	1.5	34
141	Unification of the properties of theEL2 defect in GaAs. Physical Review B, 1989, 39, 5538-5541.	1.1	34
142	Band anticrossing in dilute nitrides. Journal of Physics Condensed Matter, 2004, 16, S3355-S3372.	0.7	34
143	Metal-Insulator Transition by Isovalent Anion Substitution inGa1â^'xMnxAs: Implications to Ferromagnetism. Physical Review Letters, 2008, 101, 087203.	2.9	34
144	Temperature dependence of the band gap of ZnSe1â^'xOx. Applied Physics Letters, 2009, 95, 151907.	1.5	34

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145	Determination of effective mass in InN by high-field oscillatory magnetoabsorption spectroscopy. Physical Review B, 2011, 83, .	1.1	34
146	Electron mobility limits in a two-dimensional electron gas: GaAs-GaAlAs heterostructures. Physical Review B, 1984, 29, 4818-4820.	1.1	33
147	Direct evidence of carbon precipitates in GaAs and InP. Applied Physics Letters, 1994, 65, 1145-1147.	1.5	33
148	High-temperature Hall effect inGa1â^'xMnxAs. Physical Review B, 2004, 69, .	1.1	33
149	GaN1â^'xBix: Extremely mismatched semiconductor alloys. Applied Physics Letters, 2010, 97, 141919.	1.5	33
150	Response to â€˜â€˜Comment on â€˜Electron mobility in modulation-doped heterostructuresâ€™ â€™â€™. Physical Review B, 1985, 32, 2645-2646.	1.1	32
151	Si doping of high-Al-mole fraction AlxGa1â^'xN alloys with rf plasma-induced molecular-beam-epitaxy. Applied Physics Letters, 2002, 81, 5192-5194.	1.5	32
152	Defects and properties of cadmium oxide based transparent conductors. Journal of Applied Physics, 2016, 119, .	1.1	32
153	Enhanced diffusion in nonstoichiometric quantum wells and the decay of supersaturated vacancy concentrations. Applied Physics Letters, 1996, 69, 239-241.	1.5	31
154	Band anticrossing in group II-Oxâ€“VI1â^'x highly mismatched alloys: Cd1â^'xMnyOxTe1â^'x quaternaries synthesized by O ion implantation. Applied Physics Letters, 2002, 80, 1571-1573.	1.5	31
155	Probing and modulating surface electron accumulation in InN by the electrolyte gated Hall effect. Applied Physics Letters, 2008, 93, .	1.5	31
156	Effects of rapid quenching on the impurity site location in Znâ€diffused InP. Journal of Applied Physics, 1993, 74, 86-90.	1.1	30
157	Growth of Thick InN by Molecular Beam Epitaxy. Materials Research Society Symposia Proceedings, 2002, 743, L4.10.1.	0.1	30
158	Hole mobility in modulation-doped heterostructures: GaAs-AlGaAs. Physical Review B, 1985, 31, 5557-5560.	1.1	29
159	Nitrogen-induced enhancement of the free electron concentration in sulfur implanted GaNxAs1â^'x. Applied Physics Letters, 2000, 77, 2858-2860.	1.5	29
160	Effect of film thickness on the incorporation of Mn interstitials in Ga1â^'xMnxAs. Applied Physics Letters, 2005, 86, 042102.	1.5	29
161	High electron mobility InN. Applied Physics Letters, 2007, 90, 162103.	1.5	29
162	Effect of Sb on GaNAs Intermediate Band Solar Cells. IEEE Journal of Photovoltaics, 2013, 3, 730-736.	1.5	29

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163	Magneto-optical study of shallow donors in transmutation-doped GaAs. Journal of Physics and Chemistry of Solids, 1978, 39, 873-877.	1.9	28
164	Enhanced nitrogen incorporation by pulsed laser annealing of GaNxAs1â^'x formed by N ion implantation. Applied Physics Letters, 2002, 80, 3958-3960.	1.5	28
165	Acoustic-phonon scattering in modulation-doped heterostructures. Physical Review B, 1988, 37, 8530-8533.	1.1	27
166	Narrow band gap group III-nitride alloys. Physica E: Low-Dimensional Systems and Nanostructures, 2004, 20, 300-307.	1.3	27
167	Electronic effects determining the formation of ferromagnetic III1â^'xMnxV alloys during epitaxial growth. Physica E: Low-Dimensional Systems and Nanostructures, 2004, 25, 171-180.	1.3	27
168	Electronic band structure of ZnO-rich highly mismatched ZnO1â^'xTex alloys. Applied Physics Letters, 2015, 106, .	1.5	27
169	Highly mismatched N-rich GaN1â^'xSbx films grown by low temperature molecular beam epitaxy. Applied Physics Letters, 2013, 102, .	1.5	26
170	Charge transfer and mobility enhancement at CdO/SnTe heterointerfaces. Applied Physics Letters, 2014, 105, 132103.	1.5	26
171	On the optical evaluation of the EL2 deep level concentration in semiâ€insulating GaAs. Applied Physics Letters, 1983, 43, 192-194.	1.5	25
172	Diluted magnetic semiconductors formed by ion implantation and pulsed-laser melting. Physica B: Condensed Matter, 2003, 340-342, 908-912.	1.3	25
173	Narrow bandgap group III-nitride alloys. Physica Status Solidi (B): Basic Research, 2003, 240, 412-416.	0.7	25
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